PATENT APPLICATION

Attorney Docket No.: 2000.008.00/US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Kevin J. Yang Group Art Unit: Unknown Farid Nemati Scott Robins Examiner: Unknown James D. Plummer Atty Docket: 2000.008.00/US Hvun-Jin Cho Serial No.: Unknown Filed: Concurrently Herewith § § Title: THYRISTOR DEVICE WITH CARBON LIFETIME ADJUSTMENT IMPLANT § AND ITS METHOD OF FABRICATION

COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

This Information Disclosure Statement is submitted:

- under 37 CFR §1.97 (b) (Within three months of filing national application other than a continued prosecution application under §1.53(d); or within three months of the date of entry of the national stage as set forth in §1.491 in an international application; before mailing date of first office action on the merits; or before the mailing of a first Office action after the filing of a request for continued examination under §1.114);
- Applicant(s) submit herewith <u>Form PTO 1449</u>-Information Disclosure Citation together with copies of patents, publications or other information of which applicant(s) are aware, which applicant(s) believe(s) may be material to the examination of this application and for which there may be a duty to disclose in accordance with 37 CFR 1.56.

It is requested that the information disclosed herein be made of record in this application.

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Respectfully submitted.

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| Substitute for form 1449A/PTO | | | | Complete if Known | | |
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| _ | | | | Application Number | T | |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT FORM PTO-1449 (Modified) (USE AS MANY SHEETS AS NECESSARY) | | | | Filing Date | September 25, 2003 | |
| | | | | First Named Inventor | Kevin J. Yang | |
| | | | | Art Unit | | |
| | | | | Examiner Name | | |
| SHEET | 1 | OF | 1 | Attorney Docket Number | 2000.008.00/US | |
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U.S. PATENT DOCUMENTS Document Number Pages, Columns, Lines, Where Publication Date Examiner Cite Name of Patentee or Relevant Passages or Relevant MM-DD-YYYY Applicant of Cited Document Initials* Number- Kind Code (if known) Figures Appear US 6,462,359 10-08-02 Nemati et al. US 6,229,161 05-08-01 Nemati et al. US 4,323,793 04-06-82 Schutten et al.

| OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS | | | | | | | |
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| Examiner Initials* | Cite No.1 | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | | | | | |
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